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November 2013

FDI150N10

N-Channel PowerTrench[®] MOSFET 100 V, 57 A, 16 m Ω

Features

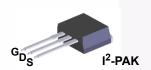
- $R_{DS(on)}$ = 12 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 49 A
- · Fast Switching Speed
- · Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{DS(on)}$
- · High Power and Current Handling Capability
- · RoHS Compliant

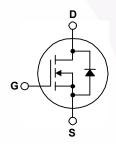
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- · Synchronous Rectification for ATX / Server / Telecom PSU
- · Battery Protection Circuit
- · Motor Drives and Uninterruptible Power Supplies
- · Micor Solar Inverter





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter			Unit
V_{DSS}	Drain to Source Voltage	:		100	V
V_{GSS}	Gate to Source Voltage			±20	V
	Drain Current	- Continuous (T _C = 25°C)		57	Α
ID	Dialii Guitelli	- Continuous (T _C = 100°C)		40	Α
I _{DM}	Drain Current	- Pulsed	(Note 1)	228	Α
E _{AS}	Single Pulsed Avalanche Energy (Note 2)			132	mJ
dv/dt	Peak Diode Recovery d	v/dt	(Note 3)	7.5	V/ns
D	Power Dissipation	(T _C = 25°C)		110	W
P_{D}	Power Dissipation	- Derate Above 25°C		0.88	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C
T _L	Maximum Lead Temper	ature for Soldering, 1/8" from Case for 5 Se	conds	300	°C

Thermal Characteristics

Symbol	Parameter	FDI150N10	Unit
$R_{ heta JC}$	Thermal Resistance, Junction to Case, Max.	1.13	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	0/00

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDI150N10	FDI150N10	I ² -PAK	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	eteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_C = 25^{\circ} C$	100	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	-	0.1	-	V/°C
1	Zero Gate Voltage Drain Current	V _{DS} = 100 V, V _{GS} = 0 V	-	-	1	^
IDSS	Zero Gate voltage Drain Current	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}, T_{C} = 150^{\circ}\text{C}$	-	-	500	μА
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±20 V, V _{DS} = 0 V	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	2.5	-	4.5	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 49 A	-	12	16	mΩ
9 _{FS}	Forward Transconductance	V _{DS} = 20 V, I _D = 49 A	-	156	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V - 25 V V - 0 V	-	3580	4760	pF
C _{oss}	Output Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	-	340	450	pF
C _{rss}	Reverse Transfer Capacitance	1 1911 12	-\	140	210	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time			-	47	104	ns
t _r	Turn-On Rise Time	$V_{DD} = 50 \text{ V}, I_{D} = 49 \text{ A},$		-	164	338	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_{G} = 25 Ω		-	86	182	ns
t _f	Turn-Off Fall Time		(Note 4)	-	83	176	ns
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 80 V, I _D = 49 A,		-	53	69	nC
Q _{gs}	Gate to Source Gate Charge	V _{GS} = 10 V		-	19	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		(Note 4)	-	15	-	nC

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	57	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		_	-	228	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 49 A	-	-	1.3	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 49 A,	-	41	-	ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt = 100 A/μs	-	70	-	nC

- 1: Repetitive rating: pulse-width limited by maximum junction temperature.
- 2: L = 0.11 mH, I $_{AS}$ = 49 A, V $_{DD}$ = 50 V, R $_{G}$ = 25 Ω , starting T $_{J}$ = 25°C.
- I_{SD} ≤ 49 A, di/dt ≤ 200 A/µs, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C.
 Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

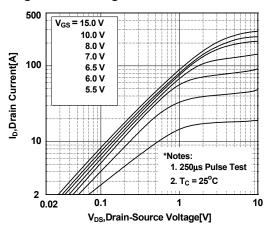


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

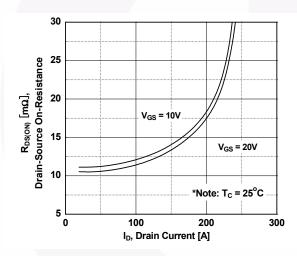


Figure 5. Capacitance Characteristics

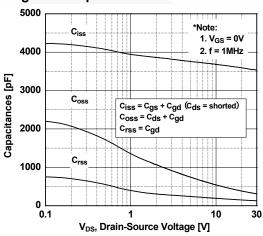


Figure 2. Transfer Characteristics

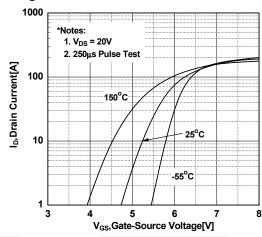


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

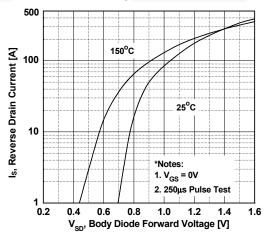
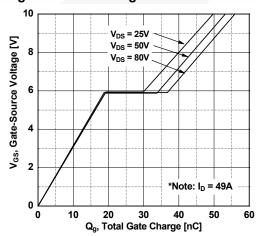


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

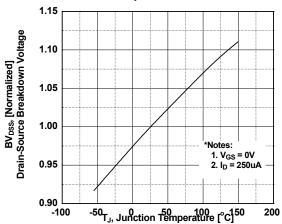


Figure 8. On-Resistance Variation vs. Temperature

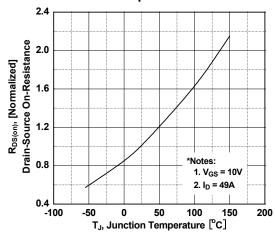


Figure 9. Maximum Safe Operating Area

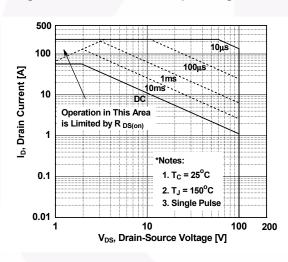


Figure 10. Maximum Drain Current vs. Case Temperature

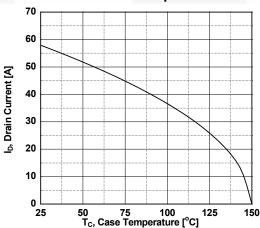
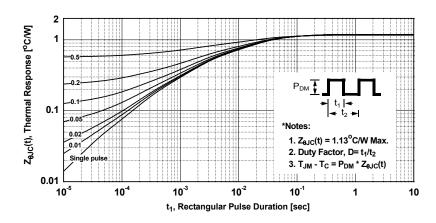


Figure 11. Transient Thermal Response Curve



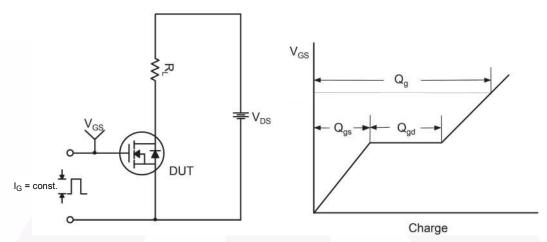


Figure 12. Gate Charge Test Circuit & Waveform

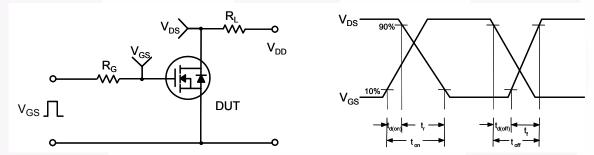


Figure 13. Resistive Switching Test Circuit & Waveforms

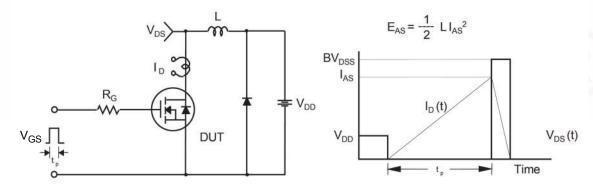


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

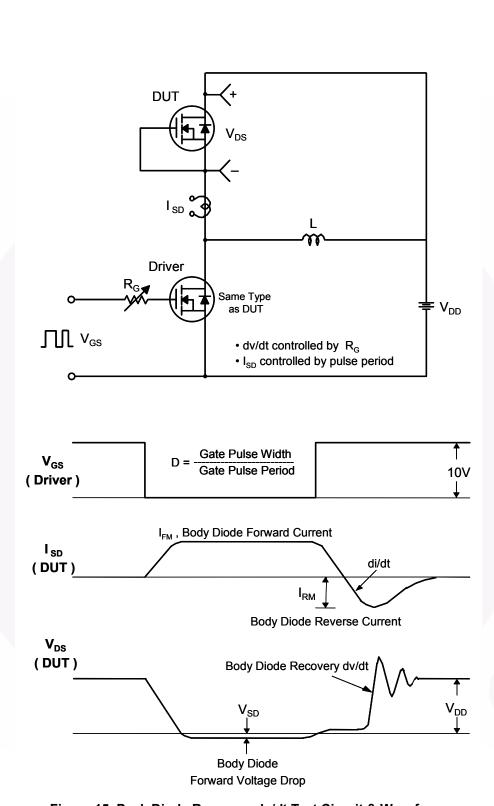
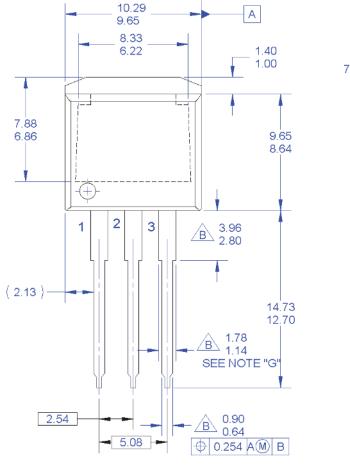
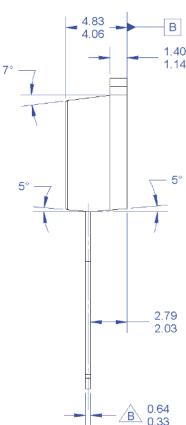


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions





NOTES:

A. EXCEPT WHERE NOTED CONFORMS TO TO262 JEDEC VARIATION AA.

B. DOES NOT COMPLY JEDEC STD. VALUE.
C. ALL DIMENSIONS ARE IN MILLIMETERS.
D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
E. DIMENSION AND TOLERANCE AS PER ANSI Y14.5-1994.
F. LOCATION OF PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF PACKAGE)
G. MAXIMUM WIDTH FOR F102 DEVICE = 1.35 MAX.
H. DRAWING FILE NAME: TO262A03REV5

Figure 16. TO262 (I²PAK), Molded, 3-Lead, Jedec Variation AA

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Preliminary First Production		Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed Full Production		Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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